## ORIGINALLY FILED AMENDMENT TRANSMITTAL LETTER Attorney Docket MICR131.02 ion Serial Number: Filing Date: Examiner: Group Art Unit: 09/503638 2/14/2000 G. Peralta Invention: RANDOM ACCESS MEMORY TO THE COMMISSIONER OF PATENTS AND TRADEMARKS: Transmitted herewith is an amendment in the above-identified application. The fee has been calculated as shown below. CLAIMS AS AMENDED NO. OF EXTRA CLAIMS REMAINING HIGHEST NUMBER RATE ADDITIONAL AFTER AMENDMENT PREVIOUSLY PAID CLAIMS PRESENT FOR TOTAL CLAIMS 11 **MINUS** 20 0 \$18 \$ 0.00 INDEP. CLAIMS 6 **MINUS** 5 1 \$84 \$ 84.00 X Petition is hereby made under 37 CFR 1.136(a) to extend the time for response the Office Action of 9/7/2001 to and through 3/7/2002, comprising an extension of the shortened statutory period of: one month (\$110) X three months (\$920) two months (\$400) four months (\$1,440) TOTAL ADDITIONAL FEE FOR THIS AMENDMENT \$1,004.00

Small entity status of this application under 37 CFR 1.9 and 1.27 has been established by

a verified statement previously submitted.

A verified statement to establish small entity status under 37 CFR 1.9 and 1.27 is enclosed.

A check in the amount of \$ 1004.00 is attached.

Charge \$ to Deposit Account

No additional fee is required.

Steven R. Ormiston Reg. No. 35974

I hereby certify that this correspondence and all correspondence identified as accompanying this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to the Assistant Commissioner for Patents, Washington,

D.C. 20231 on 3<del>17/2002</del>: 1/10reh le, 2002 HP

#8/B 4.500

COPY OF PAPERS MULLS!
ORIGINALLY FILED

In re Application of:

Kirk D. Prall, et al.

Serial No: 09/503,638

Filed: -February 14, 2000-

For: RANDOM ACCESS MEMORY

Attorney

Docket Number: MICR131.02

Group Art Unit: 2814

Examiner: G. Peralta

TECHNOLOGY CENTER 2000

March 5, 2002

Assistant Commissioner of Patents Washington, DC 20231

Sir:

## RESPONSE TO THE OFFICE ACTION MAILED SEPTEMBER 7, 2001

Please amend the Application as follows.

## In The Claims

Add the following new claims.

30.(new) A semiconductor memory device, comprising:

a substrate;

a contact region in the substrate;

a first dopant implant in the contact region, the first implant defining a first implant profile; and

a second dopant implant in the contact region, the second implant defining a second implant profile narrower and deeper than the first implant profile.

31.(new) A device according to Claim 30, wherein the first and second dopants have the same conductivity type.

32.(new) A device according to Claim 31, further comprising a capacitor in electrical contact with the contact region.